



## **DUAL P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Features**

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected up to 3kV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

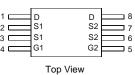
## **Mechanical Data**

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.039 grams (approximate)









Pin Configuration



Internal Schematic

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I <sub>D</sub>	6.04 3.96	А
Pulsed Drain Current (Note 4)			I <sub>DM</sub>	22	A

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P <sub>D</sub>	0.89	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C	R <sub>0JA</sub>	142.7	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 3. Device mounted on FR-4 substrate PC board with minimum recommended pad layout.
- 4. Repetitive rating, pulse width limited by junction temperature.

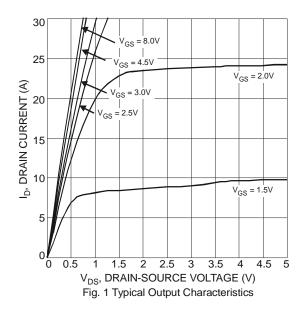


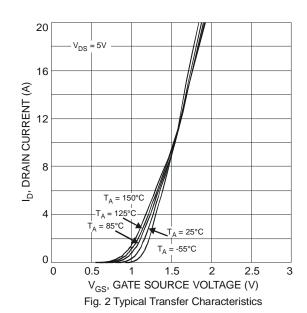
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	-0.7	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		-	23 35 30 45	35	;	$V_{GS} = -4.5V$ , $I_D = -4.0A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)				mΩ	$V_{GS} = -2.5V, I_D = -4.0A$	
	, ,		41	62		$V_{GS} = -1.8V$ , $I_D = -2.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	14	-	S	$V_{DS} = -5V, I_{D} = -4A$	
Diodes Forward Voltage	$V_{SD}$	-	-0.7	-1.0	V	$Is = -1A$ , $V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	C <sub>iss</sub>	-	1610	-	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, -f = 1.0MHz	
Output Capacitance	Coss	-	157	-	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	145	-	pF	-  = 1.0lvin2	
Gate Resistance	$R_{g}$	-	9.45	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
SWITCHING CHARACTERISTICS							
Total Gate Charge	$Q_g$	-	15.4	-	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $-I_{D} = -4A$	
Gate-Source Charge	$Q_{gs}$	-	2.5	-	nC		
Gate-Drain Charge	$Q_{gd}$	-	3.3	-	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	-	16.8	-	ns		
Turn-On Rise Time	t <sub>r</sub>	-	12.4	-	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	94.1	-	ns	$R_L = 10\Omega, R_G = 6.0\Omega, I_D = -1A$	
Turn-Off Fall Time	t <sub>f</sub>	-	42.4	-	ns		

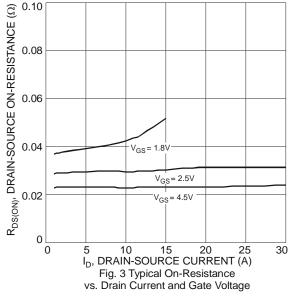
Notes: 5. Short duration pulse test used to minimize self-heating effects.

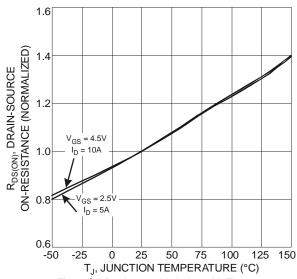
6. Guaranteed by design. Not subject to production testing.

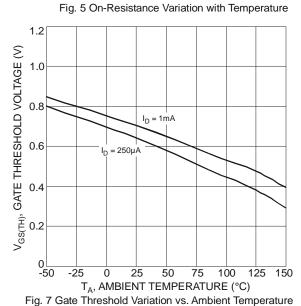


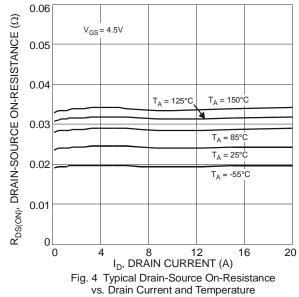












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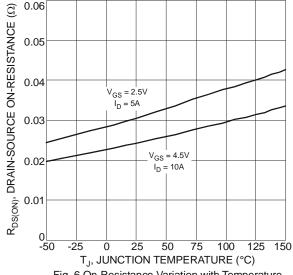


Fig. 6 On-Resistance Variation with Temperature

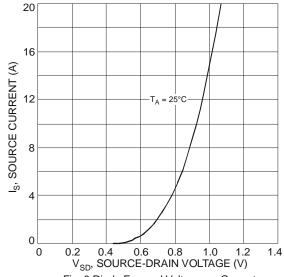
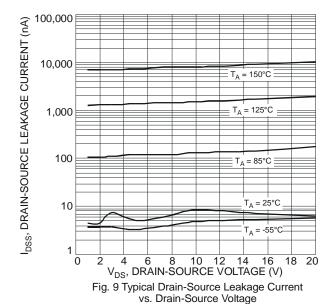
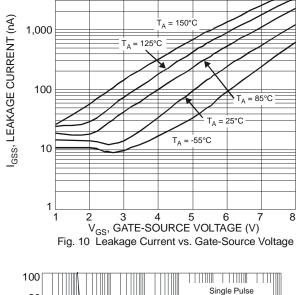


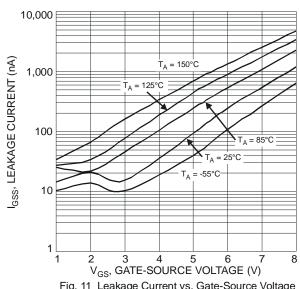
Fig. 8 Diode Forward Voltage vs. Current

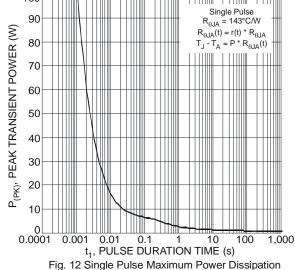


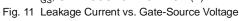


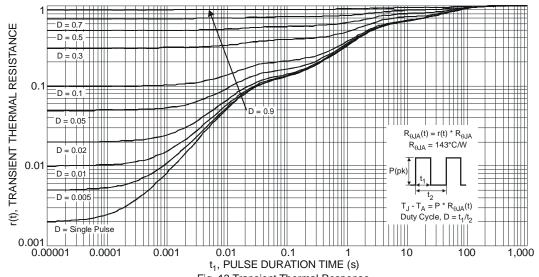


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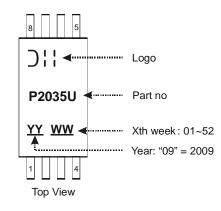


## Ordering Information (Note 7)

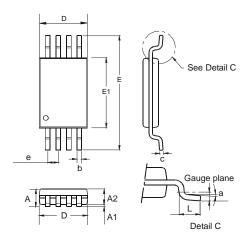
Part Number	Case	Packaging	
DMP2035UTS-13	TSSOP-8L	2500 / Tape & Reel	

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

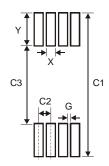


# **Package Outline Dimensions**



TSSOP-8L						
Dim	Min	Max	Тур			
а	0.09	-	_			
Α	_	1.20	_			
A1	0.05	0.15	_			
A2	0.825	1.025	0.925			
b	0.19	0.30	_			
С	0.09	0.20	-			
D	2.90	3.10	3.025			
е	_	-	0.65			
Е	_	_	6.40			
E1	4.30	4.50	4.425			
L	0.45	0.75	0.60			
All Dimensions in mm						

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Х	0.45
Υ	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20



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